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|  | <h2>SIR166DP-T1-GE3</h2>   |
|   | <p><b>Hersteller-Teilenummer:</b> SIR166DP-T1-GE3</p> <p><b>Hersteller / Marke:</b> Electro-Films (EFI) / Vishay</p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 30V 40A PPAK SO-8</p> <p><b>Datenblätter:</b>  <a href="#">SIR166DP-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 62567 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation.<br/>See specs for product details.</p>            |  |

### Spezifikationen

|  |   |
|--|---|
| Teilenummer                                      | SIR166DP-T1-GE3   |
| Hersteller                                       | Electro-Films (EFI) / Vishay  |
| Beschreibung                                     | MOSFET N-CH 30V 40A PPAK SO-8   |
| Kategorie  | <a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> , |
| Teilstatus                                       | 62567 pcs Stock   |
| Hersteller Standard Vorlaufzeit                  | 32 Weeks  |
| detaillierte Beschreibung                        | N-Channel 30V 40A (Tc) 5W (Ta), 48W (Tc) Surface                                  |
| Serie  | TrenchFET®  |
| Technologie                                      | MOSFET (Metal Oxide)  |
| Betriebstemperatur                               | -55°C ~ 150°C (TJ)  |
| Befestigungsart                                  | Surface Mount   |
| Verpackung / Gehäuse                             | PowerPAK® SO-8  |
| Supplier Device-Gehäuse                          | PowerPAK® SO-8  |
| Verlustleistung (max)                            | 5W (Ta), 48W (Tc)   |
| Typ FET  | N-Channel   |
| FET-Merkmal                                      | -   |
| Drain-Source-Spannung (Vdss)                     | 30V   |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 40A (Tc)  |
| Rds On (Max) @ Id, Vgs                           | 3.2 mOhm @ 15A, 10V   |
| VGS (th) (Max) @ Id                              | 2.2V @ 250µA  |
| Gate Charge (Qg) (Max) @ Vgs                     | 77nC @ 10V  |
| Eingabekapazität (Ciss) (Max) @ Vds              | 3340pF @ 15V  |
| Antriebsspannung (Max Rds On, Min Rds On)        | 4.5V, 10V   |
| Vgs (Max)  | ±20V  |
| Verpackung                                       | Tape & Reel (TR)  |
| Bleifreier Status / RoHS-Status                  | Lead free / RoHS Compliant  |
| Feuchtigkeitsempfindlichkeitsniveau (MSL)        | 1 (Unlimited)   |
| Andere Namen                                     | SIR166DP-T1-GE3TR   |

SIR166DP-T1-GE3 ist neu im Original, Suche SIR166DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIR166DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIR166DP-T1-GE3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

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|---|--|--|--|
|  <p><b>SIR168DP</b><br/>VB<br/>SIR168DP VB</p> |  <p><b>SIR167DP-T1-GE3</b><br/>Electro-Films (EFI) / Vishay<br/>MOSFET P-CHAN 30V<br/>POWERPAK SO-8</p> |  <p><b>SIR164DP-T1-RE3</b><br/>Electro-Films (EFI) / Vishay<br/>MOSFET N-CH 30V 50A<br/>POWERPAKSO-8</p> |  <p><b>SIR165DP-T1-GE3</b><br/>Electro-Films (EFI) / Vishay<br/>MOSFET P-CHAN 30V<br/>POWERPAK SO-8</p> |
|  <p><b>SIR166DP</b><br/>V<br/>SIR166DP V</p>   |  <p><b>SIR166DP-T1-GE3</b><br/>Vishay / Siliconix<br/>MOSFET N-CH 30V 40A PPAK<br/>SO-8</p>             |  <p><b>SIR168DP-T1-GE3</b><br/>Vishay / Siliconix<br/>MOSFET N-CH 30V 40A PPAK<br/>SO-8</p>              |  <p><b>SIR168DP-T1-GE3</b><br/>Electro-Films (EFI) / Vishay<br/>MOSFET N-CH 30V 40A PPAK<br/>SO-8</p>   |

### heiße Teile

Mehr

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|-------------------|--------------------|---------------------|--------------------|-------------------|
| ⊛ SIR-312STT32    | ↔ SIR-34ST3F       | ⇒ SIR-563ST3F       | D SIR-563ST3FM     | ↔ SIR-563ST3FN    |
| ↔ SIR-563ST3FP    | ⊛ SIR-563ST3FX     | D SIR-56SB3F        | ⇒ SIR-56ST3F       | ↔ SIR-59SSTA47    |
| ⊛ SIR11-21C/TR8   | ↔ SIR15-21C/TR8    | ⊛ SIR158DP          | ↔ SIR158DP-T1-E3   | ↔ SIR158DP-T1-GE3 |
| D SIR158DP-T1-GE3 | ⊛ SIR164ADP-T1-GE3 | ↔ SIR164DP          | ⊛ SIR164DP-T1-E3   | ↔ SIR164DP-T1-GE3 |
| ⇒ SIR164DP-T1-GE3 | ↔ SIR166DP         | ⊛ SIR166DP-T1-E3    | ↔ SIR166DP-T1-GE3  | ↔ SIR168DP        |
| ↔ SIR168DP-T1-GE3 | ⇒ SIR168DP-T1-GE3  | D SIR172ADP-T1-GE3  | ⊛ SIR172ADP-T1-GE3 | ↔ SIR172DP        |
| ⊛ SIR172DP-T1-E3  | D SIR172DP-T1-GE3  | ⇒ SIR172DP-T1-GE3   | ↔ SIR330DP-T1-GE3  | ↔ SIR330DP-T1-GE3 |
| ↔ SIR402DP-T1-GE3 | ⊛ SIR402DP-T1-GE3  | ↔ SIR403EDP-T1-GE3  | ⇒ SIR403EDP-T1-GE3 | ↔ SIR404DP        |
| ⊛ SIR404DP-T1-E3  | ↔ SIR404DP-T1-GE3  | ⊛ SIR404DP-T1-GE3   | D SIR406DP         | ↔ SIR406DP-T1-E3  |
| ↔ SIR406DP-T1-GE3 | ⊛ SIR406DP-T1-GE3  | ↔ SIR406DP-T1-GE3-S | ⊛ SIR408DP-T1-GE3  | ↔ SIR408DP-T1-GE3 |

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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